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	Þ	- 1 -	Document ID	Issue Date	Pages	Title	Current OR
		×	US 6461939 B1	20021008	11	SOI wafers and methods for producing SOI wafer	438/459
8		×	US 6417108 B1	20020709	21	◆ · · · · · · · · · · · · · · · · · · ·	438/690

	D	1 1 1	Document ID	Issue Date	Pages	Title	Current OR
П		☒	□ 🖂 JP 11087261 A 19990330 7	19990330	ŀ	METHOD AND SYSTEM FOR ION IMPLANTING OF LOW DOSAGE AMOUNT	

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		GWINN, MATTHEW CHARLES	\boxtimes						1 -	☐ JP 11087261 A	

US-PAT-NO: 6417108

DOCUMENT-IDENTIFIER: US 6417108 B1

See image for Certificate of Correction

 $ext{TITE}$:

Semiconductor substrate and method of manufacturing the same

----- KWIC -----

Application Filing Date - AD (1);

19990128

Detailed Description Text - DETX (13):

be used to prepare a semiconductor substrate as described above by referring to bonding the wafer to another substrate operating as support member at the side of the silicon oxide and then separating the bonded substrates along the and U.S. Pat. No. 5,374,564 comprises steps of forming a silicon oxide layer hydrogen gas ions or rare gas ions into the wafer from the side of the silicon oxide layer, forming a micro-bubble layer in the single crystal silicon wafer, The method disclosed in Japanese Patent Application Laid-Open No. 5-211128 on the surface of a single crystal silicon wafer substrate, implanting either micro-bubble layer to produce an SOI substrate. Then, this SOI substrate may the first embodiment of the invention.

Claims Text - CLTX (6):

forming a silicon oxide layer on the surface of a single crystal silicon

crystal silicon wafer by implanting ions selected from hydrogen ions and rare gas ions from the side of said silicon oxide layer and bonding said silicon oxide layer to a separate support member, said steps being conducted prior to wafer substrate, forming a micro-bubble layer in the inside of said single said step of removing extreme portions.

Claims Text - CLTX (18):

silicon oxide layer on the surface of a single crystal silicon wafer substrate inside of the single crystal silicon wafer by implanting ions selected from hydrogen ions and rare gas ions from the side of the silicon oxide layer, and A method according to claim 10, further comprising steps of forming a which is to become the support member, forming a micro-bubble layer in the bonding the silicon oxide layer to a separate support member, said further steps being conducted prior to said steps of removing extreme portions.

Claims Text - CLTX (19):

silicon oxide layer on the surface of a single crystal silicon wafer substrate inside of the single crystal silicon wafer by implanting ions selected from hydrogen ions and rare gas ions from the side of the silicon oxide layer, and A method according to claim 11, further comprising steps of forming which is to become the support member, forming a micro-bubble layer in the bonding the silicon oxide layer to a separate support member, said further steps being conducted prior to said steps of removing extreme portions.

JP411087261A PAT-NO:

JP 11087261 A DOCUMENT-IDENTIFIER:

METHOD AND SYSTEM FOR ION IMPLANTING OF LOW DOSAGE AMOUNT TITLE:

March 30, 1999 PUBN-DATE:

INVENTOR-INFORMATION:

NAME

GWINN, MATTHEW CHARLES

ASSIGNEE-INFORMATION:

EATON CORP

COUNTRY N/A

JP10190125 APPL-NO:

July 6, 1998 APPL-DATE:

H01L021/265, C23C014/48 , H01J037/317 INT-CL (IPC):

ABSTRACT:

PROBLEM TO BE SOLVED: To provide a method and a system for implanting ions

05/16/2003, EAST Version: 1.03.0002

at low dosage, while enabling accurate and stable control.

for ionizing a diluent, i.e., a rare gas, and a specified dopant gas an implanting the ions into a substrate S. Since the rare gas does not react with the dopant gas not with the residue of dopant covering the inner wall of an ion cause fluctuations of conductivity into the substrate, dosage of dopant ions being implanted into the substrate S is controlled accurately, especially when SOLUTION: This ion implantation system is constituted of an ion source 12 Furthermore, since the rare gas does not introduce ions or impurities which chamber 24, ions can be implanted accurately and stably at a low dosage. a low dosage is applied.

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05/16/2003, EAST Version: 1.03.0002

6057213 US-PAT-NO:

US 6057213 A DOCUMENT-IDENTIFIER:

Methods of forming polycrystalline semiconductor layers TITLE:

-- KWIC

Claims Text - CLTX (10):

6. The method of claim 5, wherein said step of implanting ions comprises implanting ions selected from the group consisting of Si, He, Ne, H and Ar.

US-PAT-NO: 6451672

DOCUMENT-IDENTIFIER: US 6451672 B1

See image for Certificate of Correction

TITE:

Method for manufacturing electronic devices in semiconductor substrates provided with gettering sites

----- KWIC -----

Brief Summary Text - BSTX (10):

of atoms/cm.sup.2) and low energy, such that gas bubbles are produced within the semiconductor substrate by subjecting it to a step of implanting light ions More recently, the prior art proposed that microvoids be produced in the a noble gas, such as helium (He). These ions are highly permeable through silicon and implanted at a high concentration (>5.times.10.sup.15 crystalline structure.

Brief Summary Text - BSTX (18):

He ions is known as a life span controlling technique and described in European Patent Application No. 0694960 by Co.Ri.M.Me., and herein incorporated by bubbles implanted beneath the active areas of an integrated electronic device. An example of a different application of microvoids produced by implanting reference, which discloses a process for producing microvoids from helium

US-PAT-NO:

5177578

DOCUMENT-IDENTIFIER:

US 5177578 A

TITLE:

Polycrystalline silicon thin film and transistor using the same

- KWIC --

Detailed Description Text - DETX (8):

To the above film forming gas and etching gas, inert gas such as rare gas, preferably, helium, neon, argon, hydrogen, etc. may be added as a diluent gas. The diluent gas is preferably used in a proportion of 1-1000 times, or more preferably 5-100 times, as much as the etching gas.

use so dilate gas